

IN THE SPECIFICATION:

Please amend the specification as follows:

Please delete the description beginning at page 3, line 26, extending through page 4,
line 15.

Please amend the description at page 3, lines 18 to 25 to read as follows:

According to an aspect of the present invention, there is provided a semiconductor device, wherein a semiconductor element which is formed in a major surface, the semiconductor substrate has a thickness between 20-60 μm , and at least some of edges where side surfaces of the semiconductor substrate and a backside surface of the major surface cross comprise curved surfaces having a radius of curvature of 0.5 to 50 μm .